Silicon Pixel Tracker (SPT) for SiD



The Tracker at ILD/SiD



- Time Projection Chamber (TPC), in ILD
 - * Measures many rφ coordinates along a track
 - ♦ Point resolution in $r\phi \approx 100 \mu m$, resolution in $z \approx 0.5 mm$
- 5 layers of Si microstrip sensors, 25 µm pitch / 50 µm readout (in SiD)
 - * Measures 5 rφ coordinates
 - ***** Resolution $r\phi \approx 5 \mu m$, resolution in $z \approx 5 mm$ (with charge division)

Beam Structure at the ILC and Implications for the Tracker



Considering the barrel:

- Physics event rate is tiny: 1.5 hits/BX over all of layer 1 (20 cm radius)
- Background is photons:
 - Converted on 300 µm Si gives 0.002 hits/cm².BX, or 6 hits/cm² for the train (in the barrel)
 - On 100 µm thick Si this is 2 hits/cm² for the train
- With 50 μ m \times 50 μ m pixels (point resolution \approx 14 μ m) the occupancy in L1 would be only 0.005% for the whole bunch train!

Integrating, Time Slicing, Bunch Stamping Options



In the barrel:

• It could be possible to integrate all events (and the background) and read in the inter-train gap

• We have to prove that the pattern recognition does not deteriorate

• Additionally, the detector becomes highly tolerant to beam-induced EMI

In the forward region:

• Time slicing or bunch stamping could be necessary due to higher backgrounds (e.g. 2-photon processes), needs studies

Pixel Tracker Based on the SiD Design



- Barrel and Forward trackers, total area = 70.3 m²
- With 50 μm × 50 μm pixels 28.1 Gpix system
- Low mass support, gas cooling
- If each chip is 8 cm × 8 cm (2.6 Mpix): 11,000 sensors is total
- Readout and sparsification scheme to be developed



Illustration of focal plane sizes, from Luppino/Burke 'Moores' law

Focal plane size doubles every 2.5 years

From: Burke, Jorden, Vu, SDW Taormina 2005

General Considerations for the SPT

- The main challenge is to reduce material and therefore power
- Sensors $\approx 100 \ \mu m$ thick, low mass support (<1% X₀ per layer in the SiD design)
- Gas cooled, power dissipation ~O(100 W), in SiD < 500 W
- Pixel size around 50 μ m \times 50 μ m (point resolution \approx 14 μ m in binary mode)
- Bunch stamping/time slicing tracker:
 - Implies on-pixel intelligence and therefore more power
 - Sinary readout and sparsification most likely, but measurement of charge centroid is not excluded
- Integrating:
 - Lowest power (due to slow readout) and low mass
 - Full pixel readout to local readout chip
 - ✤ Resolution likely to improve below 14 µm due to the use of charge centroid

We have considered two technology solutions:

- Charge Coupled Devices
- Monolithic Active Pixel Sensors

CCD-based Pixel Tracker

- CCD-based SPT could be an excellent solution
- Each CCD is read out from 4 outputs (1 or 2 outputs also possible)
 - Here 8 cm \times 4 cm CCDs, other sizes (smaller/larger) possible up to 8 cm \times 8 cm, with yield and cost implications
 - Alternating mounting on top/bottom sides also possible
- Readout chip serving 2 adjacent CCDs on the same or other side of the support
- All chips thinned to $\approx 100 \ \mu m$ and glued to the support
 - Kapton tape providing all power, clocks and signals; and glued to support
- Material budget:
 - 0.1% for CCDs (100 µm thick)
 - 0.2% X_o for kapton (rough estimate)
 - 0.45% for mechanical support, e.g. CF barrel or 5 mm-thick SiC ladders

(mechanically linked to form a barrel)



CCD-based Pixel Tracker

Excellent detection properties:

- 100% fill factor
- Epitaxial layer between 20 µm and 50 µm (signal between 1600-4000e-)
- Well capacity > 10ke-
- Full depletion possible
- Noise below 50 e- @ 10 MHz, S/N > 30
- Efficient charge transfer for small signals despite the large pixel size
- 70 m² tracker with 50×50 µm² pixels, 28 Gpixel system

• Will need *O*(10,000) 6-inch wafers – within the capabilities of at least one vendor

- Cost is comparable to the SiD estimate (\$40M)
- The technology is available with little R&D
 - CCD with 40 μ m \times 40 μ m pixels for X-ray astronomy has been made in the past
 - In process of acquiring samples
- Possible manufacturers:
 - e2V Technologies (UK)
 - DALSA (Canada)
 - Hamamatsu Photonics (Japan)

CCD-based Pixel Tracker : Power

- Full pixel readout in the inter-train gaps
- CCD details:
 - ☆ Readout time ≈ 180 ms (at 6 MHz serial rate if one output per 1 Mpix)
 - ✤ 3-phase image area, capacitance = 30 nF/phase
 - 2-phase serial register, capacitance = 40 pF/phase
 - Will use the knowledge within LCFI on low power CCD operation
- Power dissipation (approximate):
 - ✤ 130 W for parallel clocking (@ 3 V clocks)
 - ✤ 120 W for serial clocks (@ 3 V clocks)
 - ***** Source follower power \approx 210 W
 - ☆ Readout chip power ≈ 140 W
 - Total = 600 W (0.86 mW/cm²)

Solution with Monolithic Active Pixel Sensors (MAPS)

• MAPS can do all 3 readout schemes:

- Integrating
- ✤ Time slicing
- Sunch stamping (relevant experience with CALICE ASIC1)

Integrating tracker

- Functionally the same as the CCD option
- Lowest power by elimination of high gain amplifiers, comparators and logic
- ***** However:

Large pixels are not easy to make – small collection area and significant charge sharing are common

- Single sense node for high sensitivity and low noise is preferable
- Correlated double sampling on short timescale for effective noise suppression is mandatory
- Devices are unlikely to be as large as the CCDs due to lower yield



- PPD IP offered by numerous foundries for imaging
- Pinning implant to reduce dark current

• Charge transfer allows correlated double sampling and low noise (10 e- ENC quoted)

- Large area PPD pixels will have to be developed
- Charge transfer is slow (~100 ns)
- Possible problems with inefficient transfer due to small potential fluctuations in the photodiode area
- Dynamic range is small, but should not be a problem

Pixel Designs for Integrating Tracker (2)

Photogate transfer with Buried Channel CCD storage



Bunch Stamping Tracker with MAPS

First experience with the CALICE ASIC1 for MAPS-based ECAL (designed at RAL)

- Functionally very close to bunch stamping tracker
- \bullet 50 $\mu m \times$ 50 μm pixels on 0.18 μm CMOS process
- 4-diode readout with preamplifier, targets S/N > 10
- Time stamping at ≥150 ns intervals
- On-chip data storage of up to 3 hits/pixel with 13-bit timestamp
- Binary readout
- ≈10% dead area in strips due to the space needed for data storage

• Presently the power is 7.2 mW/cm², including 1% duty factor (i.e. the analogue sections are *ON* for 1% of the time, applicable to the SPT as well)

- SPT with CALICE-like sensors could use 5 kW can this be air cooled?
- Time stamping implies analogue amplification and discrimination during the bunch train, with peak power ~100 times the average how is the material budget affected by this?

Mechanics (1)

• Geometry has been "borrowed" from the SiD design, but we have some new ideas:

- Long ladders made entirely from 8% SiC foam (5 mm thick = $0.45\% X_0$)
- Self-supporting barrel with SiC joining blocks, glued for low mass
- Additional rings (CF of SiC) and the endcaps keep it stable
- This is one of many possible implementations...



Mechanics (2)



Conclusions

- Silicon Pixel Tracker for ILC is very attractive and technologically possible
- Integrating tracker is the first option:
 - Benign backgrounds should allow it
 - CCD-based detector is possible now, with little R&D
 - MAPS-based tracker should be possible in the near future, after some R&D
 - Power requirements, mechanics and cost are comparable to the SiD microstrip design
- Bunch stamping or time slicing tracker could also be considered:
 - Power could be much higher
 - Only MAPS-based solution
 - Could be the only option for the forward disks
- Pattern recognition with integrating tracker
 - We encourage people with interest and time (LCFI has only the former!)
 - to simulate the pattern recognition in the integrating tracker
 - Time slicing or bunch stamping should be considered only if needed to improve the pattern recognition performance

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Mechanics (3)

